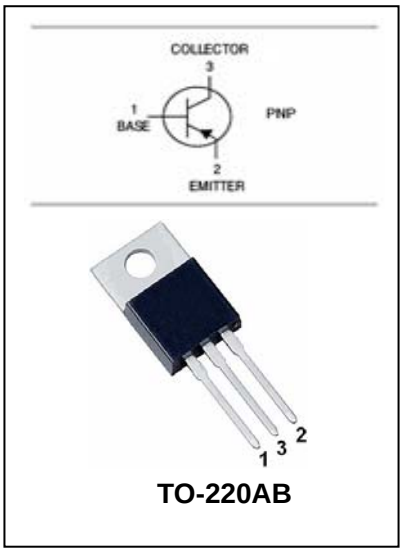
PNP Epitaxial Planar Silicon Transistors KTB1368

FEATURES

- Good Linearity of $h_{fe.}$
- Complementary to KTD2060

Lead-free



TO-220AB

MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-4	A
I_B	Base Current	-0.4	A
P_C	Collector Dissipation T_c=25℃	25	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	℃

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ELECTRICAL CHARACTERISTICS Ratings at 25℃ ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-50mA,I_B=0	-80			V
Collector Cut-off Current	I_{CBO}	V_{CB}=-80V,I_E=0			-30	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V,I_C=0			-100	μA
DC Current Gain	h_{FE}	V_{CE}=-5V,I_C=-0.5A V_{CE}=-5V,I_C=-3A	40 15		240	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-3A, I_B=-0.3A		-1.0	-1.7	V
Base-emitter Voltage	V_{BE}	I_C=-3A, V_{CE}=-5V		-1.0	-1.5	V
Transition Frequency	f_T	V_{CE}=-5V, I_E=-0.5A		9.0		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V,I_E=0, f=1MHz		130		pF

CLASSIFICATION OF h_{FE}

Range	R	O	Y
Marking	40-80	70-140	120-240

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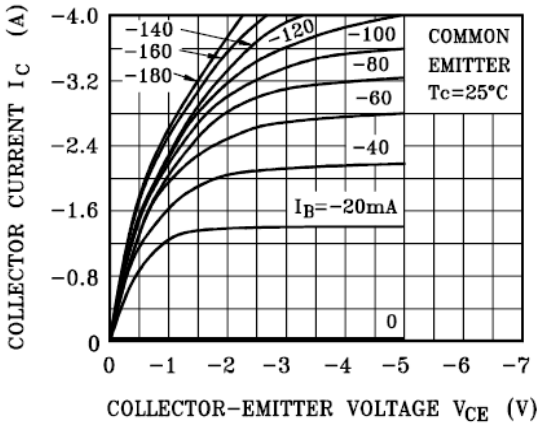
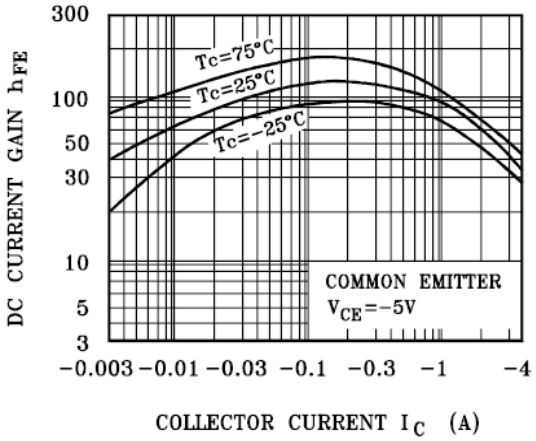
TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

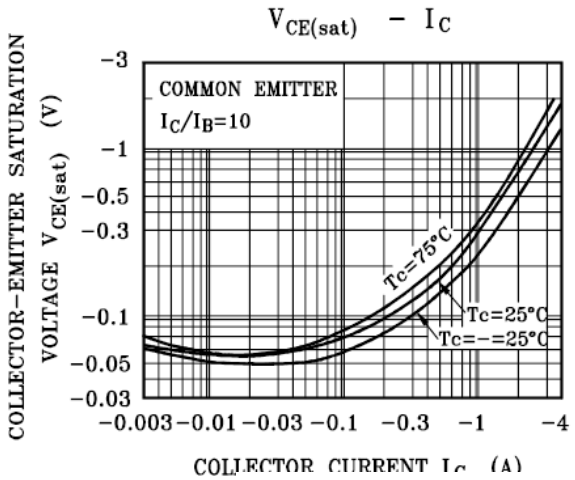
$I_C - V_{CE}$



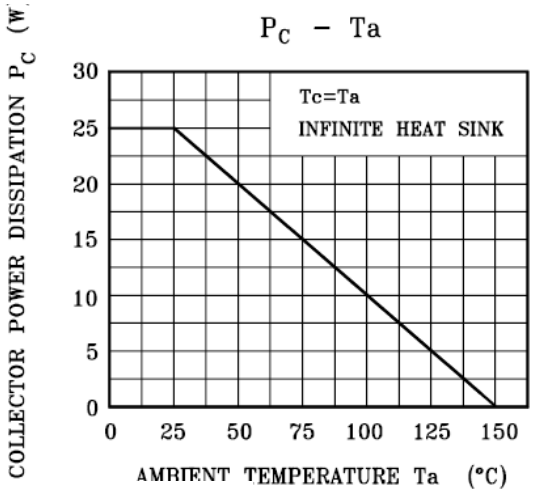
$h_{FE} - I_C$



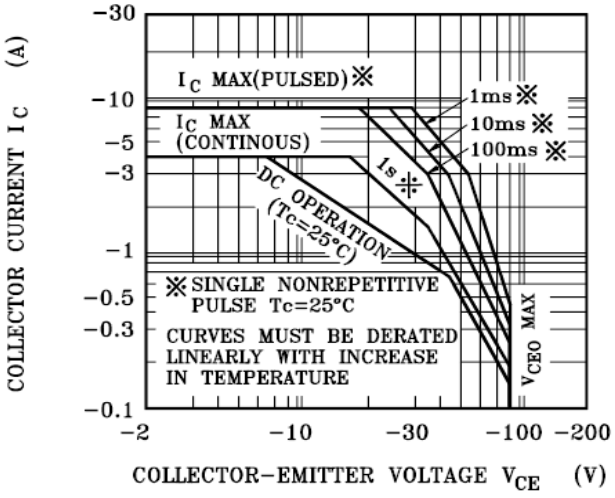
$V_{CE(sat)} - I_C$



$P_C - Ta$



SAFE OPERATING AREA



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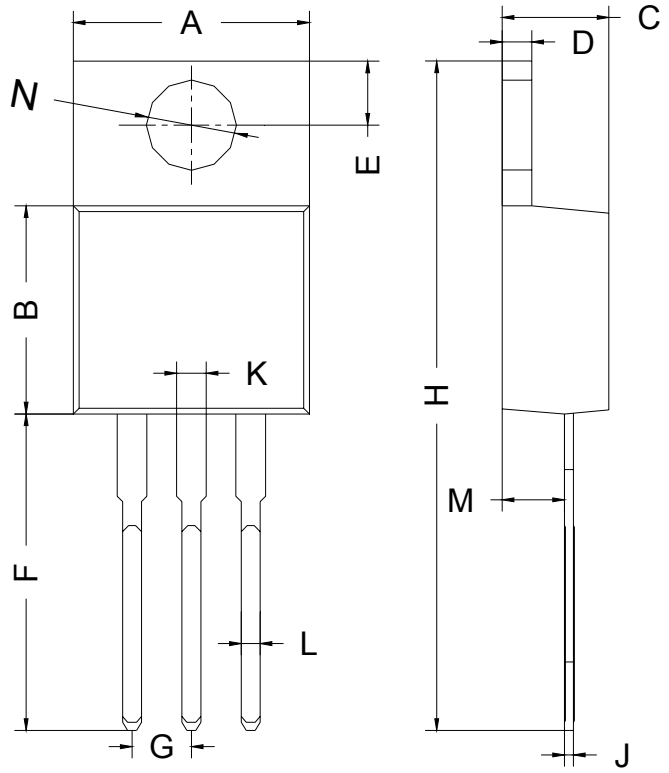
PACKAGE OUTLINE

Plastic surface mounted package TO-220AB



TO-220AB		
Dim	Min	Max
A	9.80	10.30
B	8.70	9.10
C	4.57 Typical	
D	1.27 Typical	
E	2.64	2.84
F	13.14	13.74
G	2.44	2.64
H	28.03	28.83
J	0.38 Typical	
K	1.22	1.32
L	0.71	0.91
M	2.50 Typical	
N	3.86 Typical	
All Dimensions in mm		